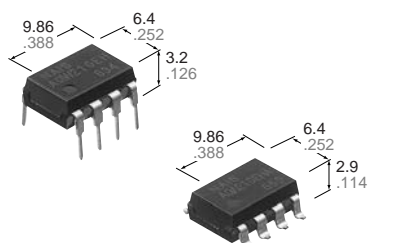


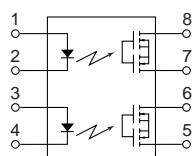
Panasonic
ideas for life

**General use and economy type.
DIP (2 Form A) 8-pin type.
Reinforced insulation
5,000V type.**

**GU-E PhotoMOS
(AQW210EH)**



mm inch



FEATURES

- 1. Reinforced insulation 5,000 V type**
More than 0.4 mm internal insulation distance between inputs and outputs. Con-forms to EN41003, EN60950 (reinforced insulation).
- 2. Compact 8-pin DIP size**
The device comes in a compact (W)6.4×(L)9.86×(H)3.2 mm (W).252×(L).388×(H).126 inch, 8-pin DIP size (through hole terminal type).
- 3. Applicable for 2 Form A use as well as two independent 1 Form A use**
- 4. Controls low-level analog signals**
PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

- 5. High sensitivity, high speed response.**
Can control a maximum 0.14 A load current with a 5 mA input current. Fast operation speed of 0.5 ms (typical). (AQW210EH)
- 6. Low-level off state leakage current**

TYPICAL APPLICATIONS

- Modem
- Telephone equipment
- Security equipment
- Sensors

TYPES

Type	I/O isolation voltage	Output rating*		Part No.				Packing quantity	
				Through hole terminal	Surface-mount terminal		Tube	Tape and reel	
					Tube packing style	Tape and reel packing style			
Load voltage	Load current		Picked from the 1/2/3/4-pin side	Picked from the 5/6/7/8-pin side					
AC/DC type	Reinforced 5,000 V	60 V	500 mA	AQW212EH	AQW212EHA	AQW212EHAX	AQW212EHAZ	1 tube contains 40 pcs. 1 batch contains 400 pcs.	1,000 pcs.
		350 V	120 mA	AQW210EH	AQW210EHA	AQW210EHAX	AQW210EHAZ		
		400 V	100 mA	AQW214EH	AQW214EHA	AQW214EHAX	AQW214EHAZ		
		600 V	40 mA	AQW216EH	AQW216EHA	AQW216EHAX	AQW216EHAZ		

*Indicate the peak AC and DC values.

Note: For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

Item		Symbol	AQW212EH(A)	AQW210EH(A)	AQW214EH(A)	AQW216EH(A)	Remarks
Input	LED forward current	I_F	50mA				
	LED reverse voltage	V_R	5V				
	Peak forward current	I_{FP}	1A				f = 100 Hz, Duty factor = 0.1%
	Power dissipation	P_{in}	75mW				
Output	Load voltage (peak AC)	V_L	60 V	350 V	400 V	600 V	
	Continuous load current (peak AC)	I_L	0.5 A (0.6 A)	0.12 A (0.14 A)	0.1 A (0.13 A)	0.04 A (0.05 A)	Peak AC, DC (): in case of using only 1 channel
	Peak load current	I_{peak}	1.5 A	0.36 A	0.3 A	0.15 A	100 ms (1 shot), $V_L = DC$
	Power dissipation	P_{out}	800mW				
Total power dissipation		P_T	850mW				
I/O isolation voltage		V_{iso}	5,000 V AC				
Temperature limits	Operating	T_{opr}	-40°C to +85°C -40°F to +185°F				Non-condensing at low temperatures
	Storage	T_{stg}	-40°C to +100°C -40°F to +212°F				

GU-E PhotoMOS (AQW210EH)

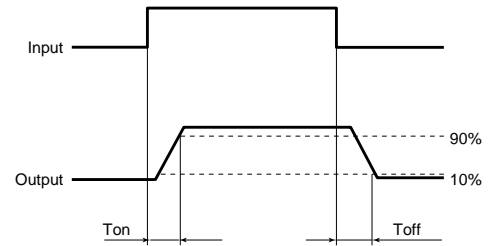
2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item		Symbol	AQW212EH(A)	AQW210EH(A)	AQW214EH(A)	AQW216EH(A)	Condition
Input	LED operate current	Typical	1.2mA				$I_L = \text{Max.}$
		Maximum	3.0mA				
	LED turn off current	Minimum	0.4mA				$I_L = \text{Max.}$
		Typical	1.1mA				
LED dropout voltage	Typical	1.25 V (1.14 V at $I_F = 5\text{mA}$)				$I_F = 50\text{mA}$	
	Maximum	1.5V					
Output	On resistance	Typical	0.83Ω	18Ω	26Ω	52Ω	$I_F = 5\text{mA}$ $I_L = \text{Max.}$ Within 1 s on time
		Maximum	2.5Ω	25Ω	35Ω	120Ω	
	Off state leakage current	Maximum	1μA				
Transfer characteristics	Turn on time*	Typical	1ms	0.5ms			$I_F = 5\text{mA}$ $I_L = \text{Max.}$
		Maximum	4ms	2.0ms			
	Turn off time*	Typical	0.08ms			0.04ms	$I_F = 5\text{mA}$ $I_L = \text{Max.}$
		Maximum	1.0ms				
	I/O capacitance	Typical	0.8pF				$f = 1\text{MHz}$ $V_B = 0\text{V}$
		Maximum	1.5pF				
Initial I/O isolation resistance	Minimum	1,000MΩ				500V DC	

Note: Recommendable LED forward current $I_F = 5$ to 10mA.

For type of connection, see catalog.

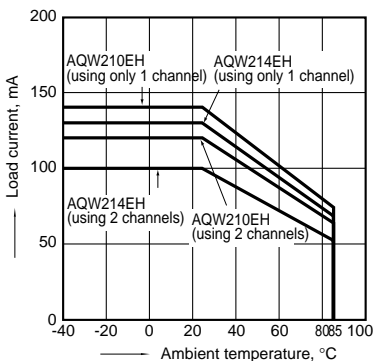
*Turn on/Turn off time



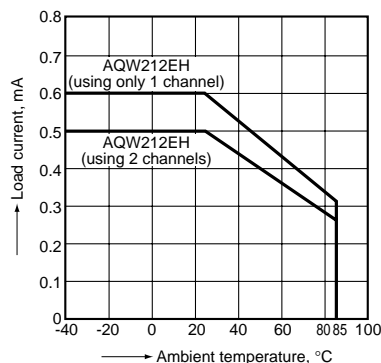
- For Dimensions, see catalog.
- For Schematic and Wiring Diagrams, see catalog.
- For Cautions for Use, see catalog.

REFERENCE DATA

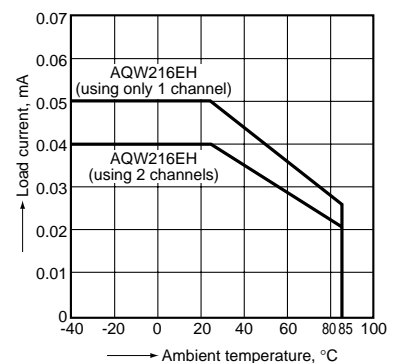
1-(1). Load current vs. ambient temperature characteristics
Allowable ambient temperature: -20°C to +85°C
-4°F to +185°F



1-(2). Load current vs. ambient temperature characteristics
Allowable ambient temperature: -40°C to +85°C
-40°F to +185°F



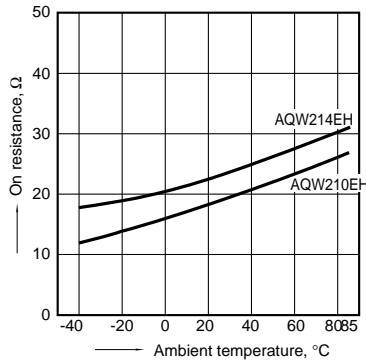
1-(3). Load current vs. ambient temperature characteristics
Allowable ambient temperature: -40°C to +85°C
-40°F to +185°F



GU-E PhotoMOS (AQW210EH)

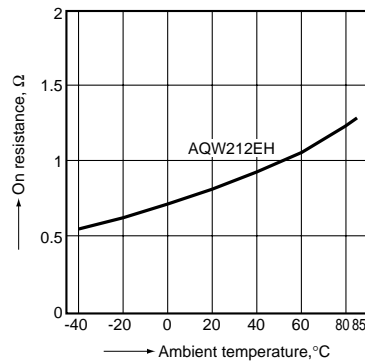
2-(1). On resistance vs. ambient temperature characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



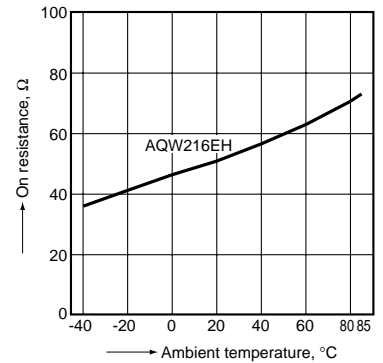
2-(2). On resistance vs. ambient temperature characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



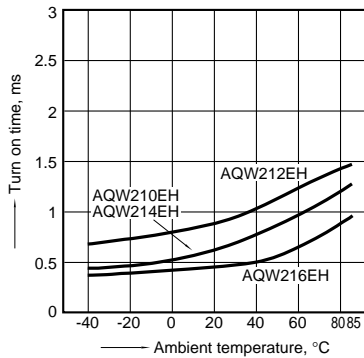
2-(3). On resistance vs. ambient temperature characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



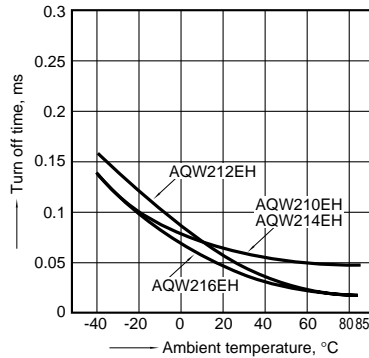
3. Turn on time vs. ambient temperature characteristics

Sample: All types
LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



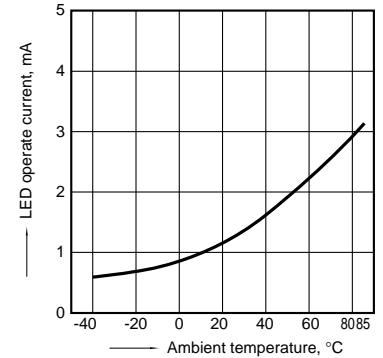
4. Turn off time vs. ambient temperature characteristics

Sample: All types
LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



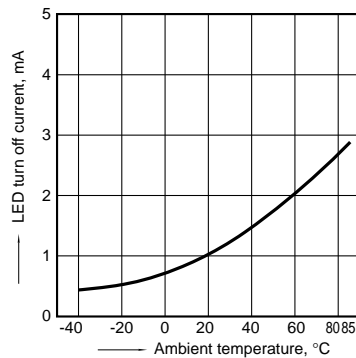
5. LED operate current vs. ambient temperature characteristics

Sample: All types; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



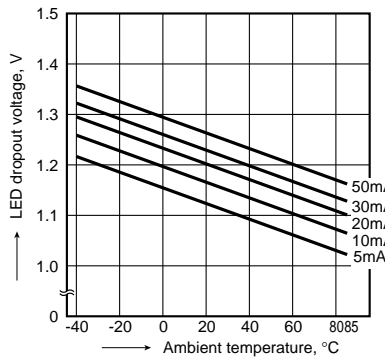
6. LED turn off current vs. ambient temperature characteristics

Sample: All types; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



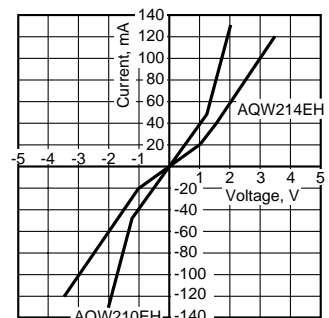
7. LED dropout voltage vs. ambient temperature characteristics

Sample: All types; LED current: 5 to 50 mA



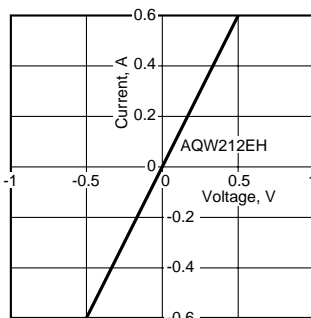
8-(1). Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 5 and 6, 7 and 8;
Ambient temperature: 25°C 77°F



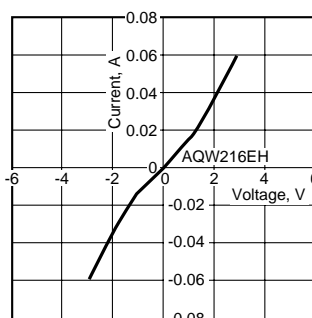
8-(2). Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 3 and 4;
Ambient temperature: 25°C 77°F



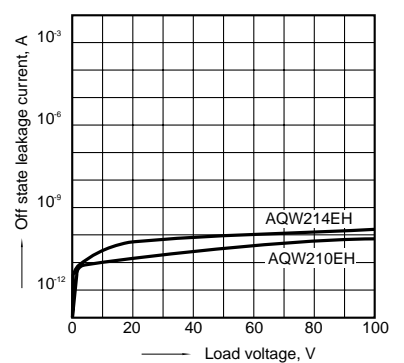
8-(3). Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 3 and 4;
Ambient temperature: 25°C 77°F



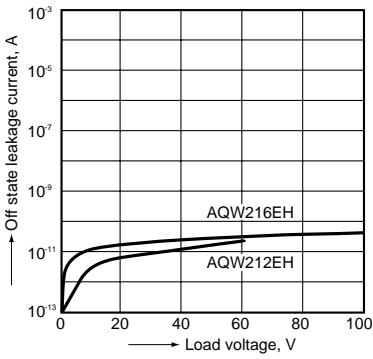
9-(1). Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Ambient temperature: 25°C 77°F

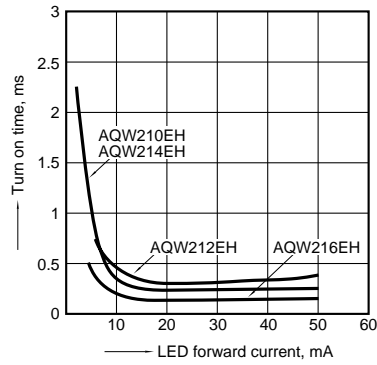


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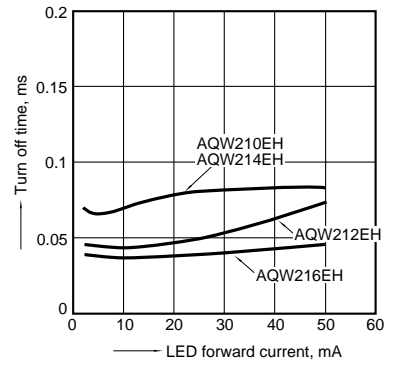
9-(2). Off state leakage current vs. load voltage characteristics
 Measured portion: between terminals 5 and 6, 7 and 8;
 Ambient temperature: 25°C 77°F



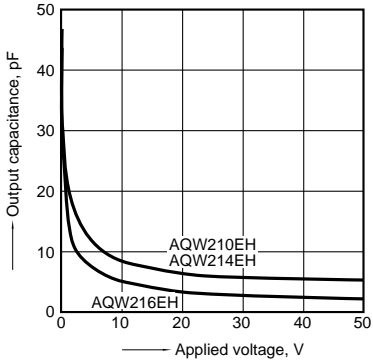
10. Turn on time vs. LED forward current characteristics
 Sample: All types
 Measured portion: between terminals 5 and 6, 7 and 8;
 Load voltage: Max. (DC); Continuous load current:
 Max. (DC); Ambient temperature: 25°C 77°F



11. Turn off time vs. LED forward current characteristics
 Sample: All types
 Measured portion: between terminals 5 and 6, 7 and 8;
 Load voltage: Max. (DC); Continuous load current:
 Max. (DC); Ambient temperature: 25°C 77°F



12-(1). Output capacitance vs. applied voltage characteristics
 Measured portion: between terminals 5 and 6, 7 and 8;
 Frequency: 1 MHz; Ambient temperature: 25°C 77°F



12-(2). Output capacitance vs. applied voltage characteristics
 Measured portion: between terminals 5 and 6, 7 and 8;
 Frequency: 1 MHz; Ambient temperature: 25°C 77°F

